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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

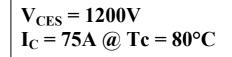


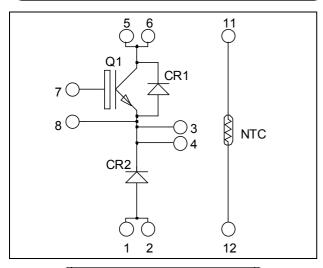


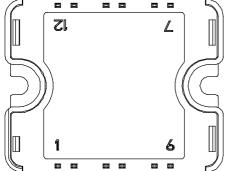




Buck chopper Fast Trench + Field Stop IGBT® Power Module







Pins 1/2; 3/4; 5/6 must be shorted together

Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

- Fast Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I _C Con	Continuous Collector Current	$T_C = 25^{\circ}C$	110	
	Continuous Conector Current	$T_C = 80$ °C	75	Α
I_{CM}	Pulsed Collector Current	$T_C = 25$ °C	175	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	357	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	150A @ 1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μΑ
V _{CE(sat)}	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$	1.4	1.7	2.1	V
		$I_{\rm C} = 75 {\rm A}$ $T_{\rm j} = 1$	$T_{j} = 125^{\circ}C$		2.0		v
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 3 \text{ mA}$		5.0		6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

·	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$\begin{aligned} V_{GE} &= 0V \\ V_{CE} &= 25V \\ f &= 1MHz \end{aligned}$			5340		pF
C_{oes}	Output Capacitance				280		
C_{res}	Reverse Transfer Capacitance				240		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)			260		
T_{r}	Rise Time	$V_{GE} = \pm 15V$			30		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 75A$			420		ns
T_{f}	Fall Time	$R_G = 4.7\Omega$		70			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_{C} = 75A$			285		ns
T_{r}	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time				520		
$T_{\rm f}$	Fall Time	$R_G = 4.7\Omega$			90		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 125$ °C		7	·	т.
E _{off}	Turn-off Switching Energy	$I_C = 75A$ $R_G = 4.7\Omega$	$T_j = 125^{\circ}C$		8.1		mJ

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
T	Maximum Reverse Leakage Current	$V_{R}=1200V$	$T_j = 25^{\circ}C$			250	۸
I_{RM}		V _R −1200 V	$T_j = 125$ °C			500	μA
I_F	DC Forward Current		Tc = 80°C		100		A
$V_{\rm F}$	Diode Forward Voltage	$I_F = 100A$	$T_i = 25$ °C		1.6	2.1	V
V F	Blode I of ward Voluge		$T_{j} = 125^{\circ}C$		1.6		,
t_{rr}	Reverse Recovery Time	_	$T_j = 25^{\circ}C$		170		ns
٩rr	Reverse Recovery Time		$T_i = 125^{\circ}C$	$T_j = 125$ °C		280	
0	Reverse Recovery Charge	$I_F = 100A$ $V_R = 600V$ $di/dt = 2000A/\mu s$	$T_j = 25$ °C		9		μС
Q_{rr}	Reverse Recovery Charge		$T_{j} = 125^{\circ}C$		18		μС
E_{r}	Reverse Recovery Energy	,	$T_j = 25^{\circ}C$		5		mJ
$\mathbf{E}_{\mathbf{r}}$			$T_{j} = 125^{\circ}C$		9		1117



Thermal and package characteristics

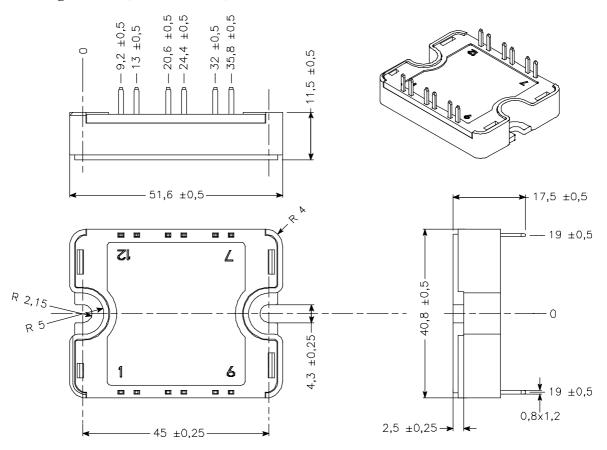
Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	Lunction to Case Thermal Resistance	IGBT			0.35	°C/W	
MthJC		Diode			0.48	C/W	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_{J}	Operating junction temperature range			-40		150	
T_{STG}	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature	-40		100			
Torque	Mounting torque	To heatsink	K M4	2.5		4.7	N.m
Wt	Package Weight	•				80	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_{T} = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature } \\ R_{T}: \text{ Thermistor value at T}$$

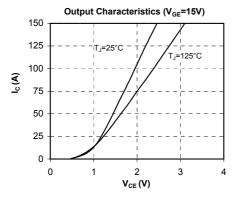
SP1 Package outline (dimensions in mm)

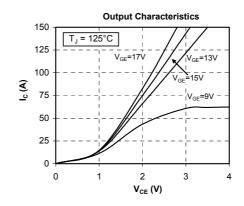


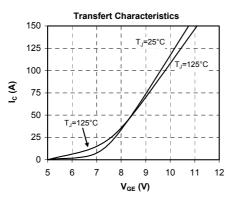
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

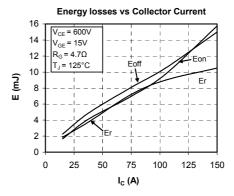


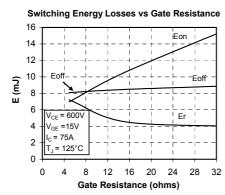
Typical Performance Curve

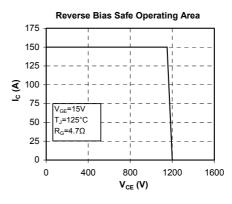


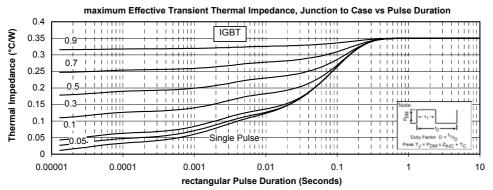




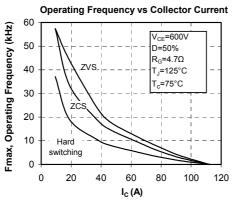




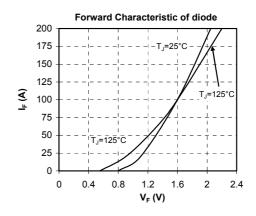


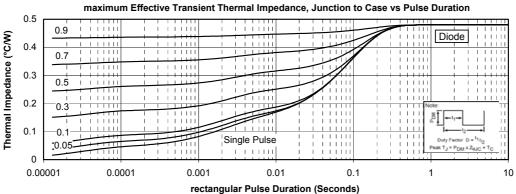






POWER PRODUCTS GROUP





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Microsemi's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.